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Understanding Embedded - FPGAs (Field Programmable Gate Array)

Embedded - FPGAs, or Field Programmable Gate Arrays, are advanced integrated circuits that offer unparalleled flexibility and performance for digital systems. Unlike traditional fixed-function logic devices, FPGAs can be programmed and reprogrammed to execute a wide array of logical operations, enabling customized functionality tailored to specific applications. This reprogrammability allows developers to iterate designs quickly and implement complex functions without the need for custom hardware.

Applications of Embedded - FPGAs

The versatility of Embedded - FPGAs makes them indispensable in numerous fields. In telecommunications.

Details

Product Status	Active
Number of LABs/CLBs	16825
Number of Logic Elements/Cells	215360
Total RAM Bits	13455360
Number of I/O	285
Number of Gates	-
Voltage - Supply	0.95V ~ 1.05V
Mounting Type	Surface Mount
Operating Temperature	0°C ~ 100°C (TJ)
Package / Case	484-FBGA, FCBGA
Supplier Device Package	484-FCBGA (19x19)
Purchase URL	https://www.e-xfl.com/product-detail/xilinx/xc7a200t-3sbg484e

Table 2: Recommended Operating Conditions⁽¹⁾⁽²⁾ (Cont'd)

Symbol	Description	Min	Typ	Max	Units
Temperature					
T_j	Junction temperature operating range for commercial (C) temperature devices	0	—	85	°C
	Junction temperature operating range for extended (E) temperature devices	0	—	100	°C
	Junction temperature operating range for industrial (I) temperature devices	–40	—	100	°C

Notes:

- All voltages are relative to ground.
- For the design of the power distribution system consult [UG483](#), 7 Series FPGAs PCB Design and Pin Planning Guide.
- Configuration data is retained even if V_{CCO} drops to 0V.
- Includes V_{CCO} of 1.2V, 1.5V, 1.8V, 2.5V, and 3.3V.
- The lower absolute voltage specification always applies.
- A total of 200 mA per bank should not be exceeded.
- V_{CCBATT} is required only when using bitstream encryption. If battery is not used, connect V_{CCBATT} to either ground or V_{CCAUX} .
- Each voltage listed requires the filter circuit described in [UG482](#): 7 Series FPGAs GTP Transceiver User Guide.
- Voltages are specified for the temperature range of $T_j = 0^\circ\text{C}$ to $+85^\circ\text{C}$.

Table 3: DC Characteristics Over Recommended Operating Conditions

Symbol	Description	Min	Typ ⁽¹⁾	Max	Units
V_{DRINT}	Data retention V_{CCINT} voltage (below which configuration data might be lost)	0.75	—	—	V
V_{DRI}	Data retention V_{CCAUX} voltage (below which configuration data might be lost)	1.5	—	—	V
I_{REF}	V_{REF} leakage current per pin	—	—	15	μA
I_L	Input or output leakage current per pin (sample-tested)	—	—	15	μA
$C_{IN}^{(2)}$	Die input capacitance at the pad	—	—	8	pF
I_{RPU}	Pad pull-up (when selected) @ $V_{IN} = 0V$, $V_{CCO} = 3.3V$	90	—	330	μA
	Pad pull-up (when selected) @ $V_{IN} = 0V$, $V_{CCO} = 2.5V$	68	—	250	μA
	Pad pull-up (when selected) @ $V_{IN} = 0V$, $V_{CCO} = 1.8V$	34	—	220	μA
	Pad pull-up (when selected) @ $V_{IN} = 0V$, $V_{CCO} = 1.5V$	23	—	150	μA
	Pad pull-up (when selected) @ $V_{IN} = 0V$, $V_{CCO} = 1.2V$	12	—	120	μA
I_{RPD}	Pad pull-down (when selected) @ $V_{IN} = 3.3V$	68	—	330	μA
	Pad pull-down (when selected) @ $V_{IN} = 1.8V$	45	—	180	μA
I_{CCADC}	Analog supply current, analog circuits in powered up state	—	—	25	mA
$I_{BATT}^{(3)}$	Battery supply current	—	—	150	nA
$R_{IN_TERM}^{(4)}$	Thevenin equivalent resistance of programmable input termination to $V_{CCO}/2$ (UNTUNED_SPLIT_40) for commercial (C), and industrial (I), and extended (E) temperature devices	28	40	55	Ω
	Thevenin equivalent resistance of programmable input termination to $V_{CCO}/2$ (UNTUNED_SPLIT_50) for commercial (C), and industrial (I), and extended (E) temperature devices	35	50	65	Ω
	Thevenin equivalent resistance of programmable input termination to $V_{CCO}/2$ (UNTUNED_SPLIT_60) for commercial (C), and industrial (I), and extended (E) temperature devices	44	60	83	Ω

Power-On/Off Power Supply Sequencing

The recommended power-on sequence is V_{CCINT} , V_{CCBRAM} , V_{CCAUX} , and V_{CCO} to achieve minimum current draw and ensure that the I/Os are 3-stated at power-on. The recommended power-off sequence is the reverse of the power-on sequence. If V_{CCINT} and V_{CCBRAM} have the same recommended voltage levels then both can be powered by the same supply and ramped simultaneously. If V_{CCAUX} and V_{CCO} have the same recommended voltage levels then both can be powered by the same supply and ramped simultaneously.

For V_{CCO} voltages of 3.3V in HR I/O banks and configuration bank 0:

- The voltage difference between V_{CCO} and V_{CCAUX} must not exceed 2.625V for longer than $T_{VCCO2VCCAUX}$ for each power-on/off cycle to maintain device reliability levels.
- The $T_{VCCO2VCCAUX}$ time can be allocated in any percentage between the power-on and power-off ramps.

The recommended power-on sequence to achieve minimum current draw for the GTP transceivers is V_{CCINT} , $V_{MGTAVCC}$, $V_{MGTAVTT}$ OR $V_{MGTAVCC}$, V_{CCINT} , $V_{MGTAVTT}$. There is no recommended sequencing for $V_{MGTVCCAUX}$. Both $V_{MGTAVCC}$ and V_{CCINT} can be ramped simultaneously. The recommended power-off sequence is the reverse of the power-on sequence to achieve minimum current draw.

If these recommended sequences are not met, current drawn from $V_{MGTAVTT}$ can be higher than specifications during power-up and power-down.

- When $V_{MGTAVTT}$ is powered before $V_{MGTAVCC}$ and $V_{MGTAVTT} - V_{MGTAVCC} > 150$ mV and $V_{MGTAVCC} < 0.7$ V, the $V_{MGTAVTT}$ current draw can increase by 460 mA per transceiver during $V_{MGTAVCC}$ ramp up. The duration of the current draw can be up to $0.3 \times T_{MGTAVCC}$ (ramp time from GND to 90% of $V_{MGTAVCC}$). The reverse is true for power-down.
- When $V_{MGTAVTT}$ is powered before V_{CCINT} and $V_{MGTAVTT} - V_{CCINT} > 150$ mV and $V_{CCINT} < 0.7$ V, the $V_{MGTAVTT}$ current draw can increase by 50 mA per transceiver during V_{CCINT} ramp up. The duration of the current draw can be up to $0.3 \times T_{VCCINT}$ (ramp time from GND to 90% of V_{CCINT}). The reverse is true for power-down.

Table 6 shows the minimum current, in addition to I_{CCQ} , that is required by Artix-7 devices for proper power-on and configuration. If the current minimums shown in Table 5 and Table 6 are met, the device powers on after all four supplies have passed through their power-on reset threshold voltages. The FPGA must not be configured until after V_{CCINT} is applied.

Once initialized and configured, use the Xilinx Power Estimator (XPE) tools to estimate current drain on these supplies.

Table 6: Power-On Current for Artix-7 Devices⁽¹⁾

Device	$I_{CCINTMIN}$	$I_{CCAUXMIN}$	I_{CCOMIN}	$I_{CCBRAMMIN}$	Units
	Typ ⁽²⁾	Typ ⁽²⁾	Typ ⁽²⁾	Typ ⁽²⁾	
XC7A100T	$I_{CCINTQ} + 170$	$I_{CCAUXQ} + 40$	$I_{CCOQ} + 40$ mA per bank	$I_{CCBRAMQ} + 60$	mA
XC7A200T	$I_{CCINTQ} + 340$	$I_{CCAUXQ} + 50$	$I_{CCOQ} + 40$ mA per bank	$I_{CCBRAMQ} + 80$	mA

Notes:

1. Use the Xilinx Power Estimator (XPE) spreadsheet tool (download at <http://www.xilinx.com/power>) to calculate maximum power-on currents.
2. Typical values are specified at nominal voltage, 25°C.

Table 7: Power Supply Ramp Time

Symbol	Description	Conditions	Min	Max	Units
T_{VCCINT}	Ramp time from GND to 90% of V_{CCINT}		0.2	50	ms
T_{VCCO}	Ramp time from GND to 90% of V_{CCO}		0.2	50	ms
T_{VCCAUX}	Ramp time from GND to 90% of V_{CCAUX}		0.2	50	ms
$T_{VCCBRAM}$	Ramp time from GND to 90% of V_{CCBRAM}		0.2	50	ms
$T_{VCCO2VCCAUX}$	Allowed time per power cycle for $V_{CCO} - V_{CCAUX} > 2.625V$	$T_J = 100^{\circ}C^{(1)}$	–	500	ms
		$T_J = 85^{\circ}C^{(1)}$	–	800	
$T_{MGTAVCC}$	Ramp time from GND to 90% of $V_{MGTAVCC}$		0.2	50	ms
$T_{MGTAVTT}$	Ramp time from GND to 90% of $V_{MGTAVTT}$		0.2	50	ms

Notes:

1. Based on 240,000 power cycles with nominal V_{CCO} of 3.3V or 36,500 power cycles with worst case V_{CCO} of 3.465V.

Table 9: Differential SelectIO DC Input and Output Levels

I/O Standard	$V_{ICM}^{(1)}$			$V_{ID}^{(2)}$			$V_{OCM}^{(3)}$			$V_{OD}^{(4)}$		
	V, Min	V, Typ	V, Max	V, Min	V, Typ	V, Max	V, Min	V, Typ	V, Max	V, Min	V, Typ	V, Max
BLVDS_25	0.300	1.200	1.425	0.100	—	—	—	1.250	—	Note 5		
MINI_LVDS_25	0.300	1.200	V_{CCAUX}	0.200	0.400	0.600	1.000	1.200	1.400	0.300	0.450	0.600
PPDS_25	0.200	0.900	V_{CCAUX}	0.100	0.250	0.400	0.500	0.950	1.400	0.100	0.250	0.400
RSDS_25	0.300	0.900	1.500	0.100	0.350	0.600	1.000	1.200	1.400	0.100	0.350	0.600
TMDS_33	2.700	2.965	3.230	0.150	0.675	1.200	$V_{CCO}-0.405$	$V_{CCO}-0.300$	$V_{CCO}-0.190$	0.400	0.600	0.800

Notes:

1. V_{ICM} is the input common mode voltage.
2. V_{ID} is the input differential voltage ($Q - \bar{Q}$).
3. V_{OCM} is the output common mode voltage.
4. V_{OD} is the output differential voltage ($Q - \bar{Q}$).
5. V_{OD} for BLVDS will vary significantly depending on topology and loading.

Table 10: Complementary Differential SelectIO DC Input and Output Levels

I/O Standard	$V_{ICM}^{(1)}$			$V_{ID}^{(2)}$		$V_{OL}^{(3)}$	$V_{OH}^{(4)}$	I_{OL}	I_{OH}
	V, Min	V, Typ	V, Max	V, Min	V, Max	V, Max	V, Min	mA, Max	mA, Min
DIFF_HSTL_I	0.300	0.750	1.125	0.100	—	0.400	$V_{CCO}-0.400$	8.00	-8.00
DIFF_HSTL_I_18	0.300	0.900	1.425	0.100	—	0.400	$V_{CCO}-0.400$	8.00	-8.00
DIFF_HSTL_II	0.300	0.750	1.125	0.100	—	0.400	$V_{CCO}-0.400$	16.00	-16.00
DIFF_HSTL_II_18	0.300	0.900	1.425	0.100	—	0.400	$V_{CCO}-0.400$	16.00	-16.00
DIFF_HSUL_12	0.300	0.600	0.850	0.100	—	20% V_{CCO}	80% V_{CCO}	0.100	-0.100
DIFF_MOBILE_DDR	0.300	0.900	1.425	0.100	—	10% V_{CCO}	90% V_{CCO}	0.100	-0.100
DIFF_SSTL135	0.300	0.675	1.000	0.100	—	$(V_{CCO}/2) - 0.150$	$(V_{CCO}/2) + 0.150$	13.0	-13.0
DIFF_SSTL135_R	0.300	0.675	1.000	0.100	—	$(V_{CCO}/2) - 0.150$	$(V_{CCO}/2) + 0.150$	8.9	-8.9
DIFF_SSTL15	0.300	0.750	1.125	0.100	—	$(V_{CCO}/2) - 0.175$	$(V_{CCO}/2) + 0.175$	13.0	-13.0
DIFF_SSTL15_R	0.300	0.750	1.125	0.100	—	$(V_{CCO}/2) - 0.175$	$(V_{CCO}/2) + 0.175$	8.9	-8.9
DIFF_SSTL18_I	0.300	0.900	1.425	0.100	—	$(V_{CCO}/2) - 0.470$	$(V_{CCO}/2) + 0.470$	8.00	-8.00
DIFF_SSTL18_II	0.300	0.900	1.425	0.100	—	$(V_{CCO}/2) - 0.600$	$(V_{CCO}/2) + 0.600$	13.4	-13.4

Notes:

1. V_{ICM} is the input common mode voltage.
2. V_{ID} is the input differential voltage ($Q - \bar{Q}$).
3. V_{OL} is the single-ended low-output voltage.
4. V_{OH} is the single-ended high-output voltage.

Speed Grade Designations

Since individual family members are produced at different times, the migration from one category to another depends completely on the status of the fabrication process for each device. [Table 12](#) correlates the current status of each Artix-7 device on a per speed grade basis.

Table 12: Artix-7 Device Speed Grade Designations

Device	Speed Grade Designations		
	Advance	Preliminary	Production
XC7A100T	-2L (0.9V)		-3, -2, -2L (1.0V), -1
XC7A200T	-2L (0.9V)		-3, -2, -2L (1.0V), -1

Production Silicon and ISE Software Status

In some cases, a particular family member (and speed grade) is released to production before a speed specification is released with the correct label (Advance, Preliminary, Production). Any labeling discrepancies are corrected in subsequent speed specification releases.

[Table 13](#) lists the production released Artix-7 device, speed grade, and the minimum corresponding supported speed specification version and ISE software revisions. The ISE software and speed specifications listed are the minimum releases required for production. All subsequent releases of software and speed specifications are valid.

Table 13: Artix-7 Device Production Software and Speed Specification Release

Device	Speed Grade		
	1.0V		0.9V
	-3	-2/-2L	-1
XC7A100T	ISE 14.4 and Vivado 2012.4 with the 14.4/2012.4 device pack v1.07		-2L
XC7A200T	ISE 14.4 and Vivado 2012.4 with the 14.4/2012.4 device pack v1.07		

Notes:

- Blank entries indicate a device and/or speed grade in advance or preliminary status.

Performance Characteristics

This section provides the performance characteristics of some common functions and designs implemented in Artix-7 devices. The numbers reported here are worst-case values; they have all been fully characterized. These values are subject to the same guidelines as the [AC Switching Characteristics, page 9](#).

Table 14: Networking Applications Interface Performances

Description	Speed Grade				Units
	1.0V			0.9V	
	-3	-2/-2L	-1	-2L	
SDR LVDS transmitter (using OSERDES; DATA_WIDTH = 4 to 8)	680	680	600	600	Mb/s
DDR LVDS transmitter (using OSERDES; DATA_WIDTH = 4 to 14)	1250	1250	950	950	Mb/s
SDR LVDS receiver (SFI-4.1) ⁽¹⁾	680	680	600	600	Mb/s
DDR LVDS receiver (SPI-4.2) ⁽¹⁾	1250	1250	950	950	Mb/s

Notes:

1. LVDS receivers are typically bounded with certain applications where specific dynamic phase-alignment (DPA) algorithms dominate deterministic performance.

Table 15: Maximum Physical Interface (PHY) Rate for Memory Interfaces⁽¹⁾⁽²⁾

Memory Standard	Speed Grade				Units
	1.0V			0.9V	
	-3	-2/-2L	-1	-2L	
4:1 Memory Controllers					
DDR3	1066	800	800	800	Mb/s
DDR3L	800	800	667	667	Mb/s
DDR2	800	800	667	667	Mb/s
LPDDR2	667	667	533	533	Mb/s
2:1 Memory Controllers					
DDR3	800	700	620	620	Mb/s
DDR3L	800	700	620	620	Mb/s
DDR2	800	700	620	620	Mb/s

Notes:

1. V_{REF} tracking is required. For more information, see [UG586, 7 Series FPGAs Memory Interface Solutions User Guide](#).
2. When using the internal V_{REF} the maximum data rate is 800 Mb/s (400 MHz).

Table 16: 3.3V IOB High Range (HR) Switching Characteristics (Cont'd)

I/O Standard	T _{IOPI}				T _{IOOP}				T _{IOTP}				Units
	Speed Grade				Speed Grade				Speed Grade				
	1.0V			0.9V	1.0V			0.9V	1.0V			0.9V	
	-3	-2/-2L	-1	-2L	-3	-2/-2L	-1	-2L	-3	-2/-2L	-1	-2L	
LVC MOS15_F4	0.77	0.86	0.93	0.98	1.85	1.97	2.23	2.27	2.42	2.63	3.06	2.92	ns
LVC MOS15_F8	0.77	0.86	0.93	0.98	1.60	1.72	1.98	2.21	2.17	2.38	2.81	2.86	ns
LVC MOS15_F12	0.77	0.86	0.93	0.98	1.35	1.47	1.73	1.96	1.92	2.13	2.56	2.61	ns
LVC MOS15_F16	0.77	0.86	0.93	0.98	1.34	1.46	1.71	1.94	1.90	2.12	2.54	2.59	ns
LVC MOS12_S4	0.87	0.95	1.02	1.08	2.57	2.69	2.95	3.18	3.14	3.35	3.78	3.83	ns
LVC MOS12_S8	0.87	0.95	1.02	1.08	2.09	2.21	2.46	2.69	2.65	2.87	3.29	3.34	ns
LVC MOS12_S12	0.87	0.95	1.02	1.08	1.79	1.91	2.17	2.40	2.36	2.57	2.99	3.05	ns
LVC MOS12_F4	0.87	0.95	1.02	1.08	1.98	2.10	2.35	2.58	2.54	2.76	3.18	3.23	ns
LVC MOS12_F8	0.87	0.95	1.02	1.08	1.54	1.66	1.92	2.15	2.11	2.32	2.75	2.80	ns
LVC MOS12_F12	0.87	0.95	1.02	1.08	1.38	1.51	1.76	1.97	1.95	2.16	2.59	2.62	ns
SSTL135_S	0.67	0.75	0.82	0.87	1.35	1.47	1.73	1.93	1.92	2.13	2.56	2.58	ns
SSTL15_S	0.60	0.68	0.75	0.80	1.30	1.43	1.68	1.88	1.87	2.09	2.51	2.53	ns
SSTL18_I_S	0.67	0.75	0.82	0.87	1.67	1.79	2.04	2.24	2.23	2.45	2.87	2.89	ns
SSTL18_II_S	0.67	0.75	0.82	0.87	1.31	1.43	1.68	1.91	1.87	2.09	2.51	2.56	ns
DIFF_SSTL135_S	0.68	0.76	0.83	0.87	1.35	1.47	1.73	1.93	1.92	2.13	2.56	2.58	ns
DIFF_SSTL15_S	0.68	0.76	0.83	0.87	1.30	1.43	1.68	1.88	1.87	2.09	2.51	2.53	ns
DIFF_SSTL18_I_S	0.71	0.79	0.86	0.87	1.68	1.80	2.06	2.24	2.25	2.46	2.89	2.89	ns
DIFF_SSTL18_II_S	0.71	0.79	0.86	0.87	1.38	1.51	1.76	1.94	1.95	2.17	2.59	2.59	ns
SSTL135_F	0.67	0.75	0.82	0.87	1.12	1.24	1.49	1.71	1.69	1.90	2.32	2.36	ns
SSTL15_F	0.60	0.68	0.75	0.80	1.07	1.19	1.45	1.68	1.64	1.85	2.28	2.33	ns
SSTL18_I_F	0.67	0.75	0.82	0.87	1.12	1.24	1.49	1.72	1.69	1.90	2.32	2.37	ns
SSTL18_II_F	0.67	0.75	0.82	0.87	1.12	1.24	1.49	1.71	1.69	1.90	2.32	2.36	ns
DIFF_SSTL135_F	0.68	0.76	0.83	0.87	1.12	1.24	1.49	1.71	1.69	1.90	2.32	2.36	ns
DIFF_SSTL15_F	0.68	0.76	0.83	0.87	1.07	1.19	1.45	1.68	1.64	1.85	2.28	2.33	ns
DIFF_SSTL18_I_F	0.71	0.79	0.86	0.87	1.23	1.35	1.60	1.80	1.79	2.01	2.43	2.45	ns
DIFF_SSTL18_II_F	0.71	0.79	0.86	0.87	1.21	1.33	1.59	1.79	1.78	1.99	2.42	2.44	ns

Table 17 specifies the values of T_{IOTPHZ} and T_{IOIBUFDISABLE}. T_{IOTPHZ} is described as the delay from the T pin to the IOB pad through the output buffer of an IOB pad, when 3-state is enabled (i.e., a high impedance state). T_{IOIBUFDISABLE} is described as the IOB delay from IBUFDISABLE to O output. In HR I/O banks, the internal IN_TERM termination turn-off time is always faster than T_{IOTPHZ} when the INTERMDISABLE pin is used.

Table 17: IOB 3-state Output Switching Characteristics

Symbol	Description	Speed Grade				Units
		1.0V			0.9V	
		-3	-2/-2L	-1	-2L	
T _{IOTPHZ}	T input to pad high-impedance	2.06	2.19	2.37	2.19	ns
T _{IOIBUFDISABLE}	IBUF turn-on time from IBUFDISABLE to O output	2.11	2.30	2.60	2.30	ns

Input Serializer/Deserializer Switching Characteristics

Table 20: ISERDES Switching Characteristics

Symbol	Description	Speed Grade				Units
		1.0V			0.9V	
		-3	-2/-2L	-1	-2L	
Setup/Hold for Control Lines						
T _{ISCK_BITSIP} / T _{ISCK_BITSIP}	BITSLIP pin setup/hold with respect to CLKDIV	0.01/0.14	0.02/0.15	0.02/0.17	0.02/0.21	ns
T _{ISCK_CE} / T _{ISCK_CE} ⁽²⁾	CE pin setup/hold with respect to CLK (for CE1)	0.45/−0.01	0.50/−0.01	0.72/−0.01	0.35/−0.11	ns
T _{ISCK_CE2} / T _{ISCK_CE2} ⁽²⁾	CE pin setup/hold with respect to CLKDIV (for CE2)	−0.10/0.33	−0.10/0.36	−0.10/0.40	−0.17/0.40	ns
Setup/Hold for Data Lines						
T _{ISDCK_D} / T _{ISCKD_D}	D pin setup/hold with respect to CLK	−0.02/0.12	−0.02/0.14	−0.02/0.17	−0.04/0.19	ns
T _{ISDCK_DDLY} / T _{ISCKD_DDLY}	DDLY pin setup/hold with respect to CLK (using IDELAY) ⁽¹⁾	−0.02/0.12	−0.02/0.14	−0.02/0.17	−0.03/0.19	ns
T _{ISDCK_D_DDR} / T _{ISCKD_D_DDR}	D pin setup/hold with respect to CLK at DDR mode	−0.02/0.12	−0.02/0.14	−0.02/0.17	−0.04/0.19	ns
T _{ISDCK_DDLY_DDR} / T _{ISCKD_DDLY_DDR}	D pin setup/hold with respect to CLK at DDR mode (using IDELAY) ⁽¹⁾	0.12/0.12	0.14/0.14	0.17/0.17	0.19/0.19	ns
Sequential Delays						
T _{ISCO_Q}	CLKDIV to out at Q pin	0.53	0.54	0.66	0.67	ns
Propagation Delays						
T _{ISDO_DO}	D input to DO output pin	0.11	0.11	0.13	0.14	ns

Notes:

1. Recorded at 0 tap value.
2. T_{ISCK_CE2} and T_{ISCK_CE2} are reported as T_{ISCK_CE}/T_{ISCK_CE} in TRACE report.

Input/Output Delay Switching Characteristics

Table 22: Input/Output Delay Switching Characteristics

Symbol	Description	Speed Grade				Units
		1.0V			0.9V	
		-3	-2/-2L	-1	-2L	
IDELAYCTRL						
T _{DLYCCO_RDY}	Reset to ready for IDELAYCTRL	3.67	3.67	3.67	3.22	μs
F _{IDELAYCTRL_REF}	Attribute REFCLK frequency = 200.00 ⁽¹⁾	200.00	200.00	200.00	200.00	MHz
	Attribute REFCLK frequency = 300.00 ⁽¹⁾	300.00	300.00	N/A	N/A	MHz
IDELAYCTRL_REF_PRECISION	REFCLK precision	±10	±10	±10	±10	MHz
T _{IDELAYCTRL_RPW}	Minimum Reset pulse width	59.28	59.28	59.28	52.00	ns
IDELAY						
T _{IDELAYRESOLUTION}	IDELAY chain delay resolution	1/(32 x 2 x F _{REF})				ps
T _{IDELAYPAT_JIT}	Pattern dependent period jitter in delay chain for clock pattern. ⁽²⁾	0	0	0	0	ps per tap
	Pattern dependent period jitter in delay chain for random data pattern (PRBS 23) ⁽³⁾	±5	±5	±5	±5	ps per tap
	Pattern dependent period jitter in delay chain for random data pattern (PRBS 23) ⁽⁴⁾	±9	±9	±9	±9	ps per tap
T _{IDELAY_CLK_MAX}	Maximum frequency of CLK input to IDELAY	680.00	680.00	600.00	520.00	MHz
T _{IDCCK_CE} / T _{IDCKC_CE}	CE pin setup/hold with respect to C for IDELAY	0.12/0.11	0.16/0.13	0.21/0.16	0.14/0.16	ns
T _{IDCCK_INC} / T _{IDCKC_INC}	INC pin setup/hold with respect to C for IDELAY	0.12/0.16	0.14/0.18	0.16/0.22	0.10/0.23	ns
T _{IDCCK_RST} / T _{IDCKC_RST}	RST pin setup/hold with respect to C for IDELAY	0.15/0.09	0.16/0.11	0.18/0.14	0.22/0.19	ns
T _{IDDO_IDATAIN}	Propagation delay through IDELAY	Note 5	Note 5	Note 5	Note 5	ps

Notes:

1. Average Tap Delay at 200 MHz = 78 ps, at 300 MHz = 52 ps.
2. When HIGH_PERFORMANCE mode is set to TRUE or FALSE.
3. When HIGH_PERFORMANCE mode is set to TRUE.
4. When HIGH_PERFORMANCE mode is set to FALSE.
5. Delay depends on IDELAY tap setting. See TRACE report for actual values.

CLB Distributed RAM Switching Characteristics (SLICEM Only)

Table 25: CLB Distributed RAM Switching Characteristics

Symbol	Description	Speed Grade				Units
		1.0V			0.9V	
		-3	-2/-2L	-1	-2L	
Sequential Delays						
T _{SHCKO}	Clock to A – B outputs	0.98	1.09	1.32	1.54	ns, Max
T _{SHCKO_1}	Clock to AMUX – BMUX outputs	1.37	1.53	1.86	2.18	ns, Max
Setup and Hold Times Before/After Clock CLK						
T _{DS_LRAM} /T _{DH_LRAM}	A – D inputs to CLK	0.54/0.28	0.60/0.30	0.72/0.35	0.96/0.40	ns, Min
T _{AS_LRAM} /T _{AH_LRAM}	Address An inputs to clock	0.27/0.55	0.30/0.60	0.37/0.70	0.43/0.71	ns, Min
	Address An inputs through MUXs and/or carry logic to clock	0.69/0.18	0.77/0.21	0.94/0.26	1.11/0.29	ns, Min
T _{WS_LRAM} /T _{WH_LRAM}	WE input to clock	0.38/0.10	0.43/0.12	0.53/0.17	0.62/0.13	ns, Min
T _{CECK_LRAM} / T _{CKCE_LRAM}	CE input to CLK	0.39/0.10	0.44/0.11	0.53/0.17	0.63/0.12	ns, Min
Clock CLK						
T _{MPW_LRAM}	Minimum pulse width	1.05	1.13	1.25	0.82	ns, Min
T _{MCP}	Minimum clock period	2.10	2.26	2.50	1.64	ns, Min

Notes:

1. A Zero "0" Hold Time listing indicates no hold time or a negative hold time.
2. T_{SHCKO} also represents the CLK to XMUX output. Refer to TRACE report for the CLK to XMUX path.

CLB Shift Register Switching Characteristics (SLICEM Only)

Table 26: CLB Shift Register Switching Characteristics

Symbol	Description	Speed Grade				Units
		1.0V			0.9V	
		-3	-2/-2L	-1	-2L	
Sequential Delays						
T _{REG}	Clock to A – D outputs	1.19	1.33	1.61	1.89	ns, Max
T _{REG_MUX}	Clock to AMUX – DMUX output	1.58	1.77	2.15	2.53	ns, Max
T _{REG_M31}	Clock to DMUX output via M31 output	1.12	1.23	1.46	1.68	ns, Max
Setup and Hold Times Before/After Clock CLK						
T _{WS_SHFREG} / T _{WH_SHFREG}	WE input	0.37/0.10	0.41/0.12	0.51/0.17	0.59/0.13	ns, Min
T _{CECK_SHFREG} / T _{CKCE_SHFREG}	CE input to CLK	0.37/0.10	0.42/0.11	0.52/0.17	0.60/0.12	ns, Min
T _{DS_SHFREG} / T _{DH_SHFREG}	A – D inputs to CLK	0.33/0.34	0.37/0.37	0.44/0.43	0.54/0.47	ns, Min
Clock CLK						
T _{MPW_SHFREG}	Minimum pulse width	0.77	0.86	0.98	1.04	ns, Min

Notes:

1. A Zero "0" Hold Time listing indicates no hold time or a negative hold time.

Block RAM and FIFO Switching Characteristics

Table 27: Block RAM and FIFO Switching Characteristics

Symbol	Description	Speed Grade				Units
		1.0V			0.9V	
		-3	-2/-2L	-1	-2L	
Block RAM and FIFO Clock-to-Out Delays						
T _{RCKO_DO} and T _{RCKO_DO_REG} ⁽¹⁾	Clock CLK to DOUT output (without output register) ⁽²⁾⁽³⁾	1.85	2.13	2.46	2.87	ns, Max
	Clock CLK to DOUT output (with output register) ⁽⁴⁾⁽⁵⁾	0.64	0.74	0.89	1.02	ns, Max
T _{RCKO_DO_ECC} and T _{RCKO_DO_ECC_REG}	Clock CLK to DOUT output with ECC (without output register) ⁽²⁾⁽³⁾	2.77	3.04	3.84	5.30	ns, Max
	Clock CLK to DOUT output with ECC (with output register) ⁽⁴⁾⁽⁵⁾	0.73	0.81	0.94	1.11	ns, Max
T _{RCKO_DO_CASCOUT} and T _{RCKO_DO_CASCOUT_REG}	Clock CLK to DOUT output with cascade (without output register) ⁽²⁾	2.61	2.88	3.30	3.76	ns, Max
	Clock CLK to DOUT output with cascade (with output register) ⁽⁴⁾	1.16	1.28	1.46	1.56	ns, Max
T _{RCKO_FLAGS}	Clock CLK to FIFO flags outputs ⁽⁶⁾	0.76	0.87	1.05	1.14	ns, Max
T _{RCKO_POINTERS}	Clock CLK to FIFO pointers outputs ⁽⁷⁾	0.94	1.02	1.15	1.30	ns, Max
T _{RCKO_PARITY_ECC}	Clock CLK to ECCPARITY in ECC encode only mode	0.78	0.85	0.94	1.10	ns, Max
T _{RCKO_SDBIT_ECC} and T _{RCKO_SDBIT_ECC_REG}	Clock CLK to BITERR (without output register)	2.56	2.81	3.55	4.90	ns, Max
	Clock CLK to BITERR (with output register)	0.68	0.76	0.89	1.05	ns, Max
T _{RCKO_RDADDR_ECC} and T _{RCKO_RDADDR_ECC_REG}	Clock CLK to RDADDR output with ECC (without output register)	0.75	0.88	1.07	1.15	ns, Max
	Clock CLK to RDADDR output with ECC (with output register)	0.84	0.93	1.08	1.29	ns, Max
Setup and Hold Times Before/After Clock CLK						
T _{RCKCK_ADDRA} /T _{RCKKC_ADDRA}	ADDR inputs ⁽⁸⁾	0.45/0.31	0.49/0.33	0.57/0.36	0.77/0.45	ns, Min
T _{RDCK_DI_WF_NC} / T _{RCKD_DI_WF_NC}	Data input setup/hold time when block RAM is configured in WRITE_FIRST or NO_CHANGE mode ⁽⁹⁾	0.58/0.60	0.65/0.63	0.74/0.67	0.92/0.76	ns, Min
T _{RDCK_DI_RF} /T _{RCKD_DI_RF}	Data input setup/hold time when block RAM is configured in READ_FIRST mode ⁽⁹⁾	0.20/0.29	0.22/0.34	0.25/0.41	0.29/0.38	ns, Min
T _{RDCK_DI_ECC} /T _{RCKD_DI_ECC}	DIN inputs with block RAM ECC in standard mode ⁽⁹⁾	0.50/0.43	0.55/0.46	0.63/0.50	0.78/0.54	ns, Min
T _{RDCK_DI_ECCW} / T _{RCKD_DI_ECCW}	DIN inputs with block RAM ECC encode only ⁽⁹⁾	0.93/0.43	1.02/0.46	1.17/0.50	1.38/0.48	ns, Min
T _{RDCK_DI_ECC_FIFO} / T _{RCKD_DI_ECC_FIFO}	DIN inputs with FIFO ECC in standard mode ⁽⁹⁾	1.04/0.56	1.15/0.59	1.32/0.64	1.55/0.77	ns, Min
T _{RCKCK_INJECTBITERR} / T _{RCKKC_INJECTBITERR}	Inject single/double bit error in ECC mode	0.58/0.35	0.64/0.37	0.74/0.40	0.92/0.48	ns, Min
T _{RCKCK_EN} /T _{RCKKC_EN}	Block RAM enable (EN) input	0.35/0.20	0.39/0.21	0.45/0.23	0.57/0.26	ns, Min
T _{RCKCK_REGCE} /T _{RCKKC_REGCE}	CE input of output register	0.24/0.15	0.29/0.15	0.36/0.16	0.40/0.19	ns, Min
T _{RCKCK_RSTREG} /T _{RCKKC_RSTREG}	Synchronous RSTREG input	0.29/0.07	0.32/0.07	0.35/0.07	0.41/0.07	ns, Min

Table 27: Block RAM and FIFO Switching Characteristics (Cont'd)

Symbol	Description	Speed Grade				Units
		1.0V			0.9V	
		-3	-2/-2L	-1	-2L	
$T_{RCKK_RSTRAM}/T_{RCKC_RSTRAM}$	Synchronous RSTRAM input	0.32/0.42	0.34/0.43	0.36/0.46	0.40/0.47	ns, Min
$T_{RCKK_WEA}/T_{RCKC_WEA}$	Write enable (WE) input (block RAM only)	0.44/0.18	0.48/0.19	0.54/0.20	0.64/0.23	ns, Min
$T_{RCKK_WREN}/T_{RCKC_WREN}$	WREN FIFO inputs	0.46/0.30	0.46/0.35	0.47/0.43	0.77/0.44	ns, Min
$T_{RCKK_RDEN}/T_{RCKC_RDEN}$	RDEN FIFO inputs	0.42/0.30	0.43/0.35	0.43/0.43	0.71/0.44	ns, Min
Reset Delays						
T_{RCO_FLAGS}	Reset RST to FIFO flags/pointers ⁽¹⁰⁾	0.90	0.98	1.10	1.25	ns, Max
$T_{RREC_RST}/T_{RREM_RST}$	FIFO reset recovery and removal timing ⁽¹¹⁾	1.87/–0.81	2.07/–0.81	2.37/–0.81	2.44/–0.71	ns, Max
Maximum Frequency						
$F_{MAX_BRAM_WF_NC}$	Block RAM (write first and no change modes) when not in SDP RF mode	509.68	460.83	388.20	315.66	MHz
$F_{MAX_BRAM_RF_PERFORMANCE}$	Block RAM (read first, performance mode) when in SDP RF mode but no address overlap between port A and port B	509.68	460.83	388.20	315.66	MHz
$F_{MAX_BRAM_RF_DELAYED_WRITE}$	Block RAM (read first, delayed write mode) when in SDP RF mode and there is possibility of overlap between port A and port B addresses	447.63	404.53	339.67	268.96	MHz
$F_{MAX_CAS_WF_NC}$	Block RAM cascade (write first, no change mode) when cascade but not in RF mode	467.07	418.59	345.78	273.30	MHz
$F_{MAX_CAS_RF_PERFORMANCE}$	Block RAM cascade (read first, performance mode) when in cascade with RF mode and no possibility of address overlap/one port is disabled	467.07	418.59	345.78	273.30	MHz
$F_{MAX_CAS_RF_DELAYED_WRITE}$	When in cascade RF mode and there is a possibility of address overlap between port A and port B	405.35	362.19	297.35	226.60	MHz
F_{MAX_FIFO}	FIFO in all modes without ECC	509.68	460.83	388.20	315.66	MHz
F_{MAX_ECC}	Block RAM and FIFO in ECC configuration	410.34	365.10	297.53	215.38	MHz

Notes:

- TRACE will report all of these parameters as T_{RCKO_DO} .
- T_{RCKO_DOR} includes T_{RCKO_DOW} , T_{RCKO_DOPR} , and T_{RCKO_DOPW} as well as the B port equivalent timing parameters.
- These parameters also apply to synchronous FIFO with $DO_REG = 0$.
- T_{RCKO_DO} includes T_{RCKO_DOP} as well as the B port equivalent timing parameters.
- These parameters also apply to multirate (asynchronous) and synchronous FIFO with $DO_REG = 1$.
- T_{RCKO_FLAGS} includes the following parameters: T_{RCKO_AEMPTY} , T_{RCKO_AFULL} , T_{RCKO_EMPTY} , T_{RCKO_FULL} , T_{RCKO_RDERR} , T_{RCKO_WRERR} .
- $T_{RCKO_POINTERS}$ includes both $T_{RCKO_RDCOUNT}$ and $T_{RCKO_WRCOUNT}$.
- The ADDR setup and hold must be met when EN is asserted (even when WE is deasserted). Otherwise, block RAM data corruption is possible.
- These parameters include both A and B inputs as well as the parity inputs of A and B.
- T_{RCO_FLAGS} includes the following flags: AEMPTY, AFULL, EMPTY, FULL, RDERR, WRERR, RDCOUNT, and WRCOUNT.
- RDEN and WREN must be held Low prior to and during reset. The FIFO reset must be asserted for at least five positive clock edges of the slowest clock (WRCLK or RDCLK).

Table 28: DSP48E1 Switching Characteristics (Cont'd)

Symbol	Description	Speed Grade				Units
		1.0V			0.9V	
		-3	-2/-2L	-1	-2L	
Setup and Hold Times of the RST Pins						
T _{DSPDCK_{RSTA; RSTB}_{AREG; BREG}/T_{DSPCKD_{RSTA; RSTB}_{AREG; BREG}}}	{RSTA, RSTB} input to {A, B} register CLK	0.41/ 0.11	0.46/ 0.13	0.55/ 0.15	0.63/ 0.40	ns
T _{DSPDCK_RSTC_CREG/T_{DSPCKD_RSTC_CREG}}	RSTC input to C register CLK	0.07/ 0.10	0.08/ 0.11	0.09/ 0.12	0.13/ 0.11	ns
T _{DSPDCK_RSTD_DREG/T_{DSPCKD_RSTD_DREG}}	RSTD input to D register CLK	0.44/ 0.07	0.50/ 0.08	0.59/ 0.09	0.67/ 0.08	ns
T _{DSPDCK_RSTM_MREG/T_{DSPCKD_RSTM_MREG}}	RSTM input to M register CLK	0.21/ 0.22	0.23/ 0.24	0.27/ 0.28	0.28/ 0.35	ns
T _{DSPDCK_RSTP_PREG/T_{DSPCKD_RSTP_PREG}}	RSTP input to P register CLK	0.27/ 0.01	0.30/ 0.01	0.35/ 0.01	0.43/ 0.00	ns
Combinatorial Delays from Input Pins to Output Pins						
T _{DSPDO_A_CARRYOUT_MULT}	A input to CARRYOUT output using multiplier	3.79	4.35	5.18	6.61	ns
T _{DSPDO_D_P_MULT}	D input to P output using multiplier	3.72	4.26	5.07	6.41	ns
T _{DSPDO_B_P}	B input to P output not using multiplier	1.53	1.75	2.08	2.48	ns
T _{DSPDO_C_P}	C input to P output	1.33	1.53	1.82	2.22	ns
Combinatorial Delays from Input Pins to Cascading Output Pins						
T _{DSPDO_{A; B}_{ACOUT; BCOUT}}	{A, B} input to {ACOUT, BCOUT} output	0.55	0.63	0.74	0.87	ns
T _{DSPDO_{A, B}_CARRYCASCOUT_MULT}	{A, B} input to CARRYCASCOUT output using multiplier	4.06	4.65	5.54	7.03	ns
T _{DSPDO_D_CARRYCASCOUT_MULT}	D input to CARRYCASCOUT output using multiplier	3.97	4.54	5.40	6.81	ns
T _{DSPDO_{A, B}_CARRYCASCOUT}	{A, B} input to CARRYCASCOUT output not using multiplier	1.77	2.03	2.41	2.88	ns
T _{DSPDO_C_CARRYCASCOUT}	C input to CARRYCASCOUT output	1.58	1.81	2.15	2.62	ns
Combinatorial Delays from Cascading Input Pins to All Output Pins						
T _{DSPDO_ACIN_P_MULT}	ACIN input to P output using multiplier	3.65	4.19	5.00	6.40	ns
T _{DSPDO_ACIN_P}	ACIN input to P output not using multiplier	1.37	1.57	1.88	2.44	ns
T _{DSPDO_ACIN_ACOUT}	ACIN input to ACOUT output	0.38	0.44	0.53	0.63	ns
T _{DSPDO_ACIN_CARRYCASCOUT_MULT}	ACIN input to CARRYCASCOUT output using multiplier	3.90	4.47	5.33	6.79	ns
T _{DSPDO_ACIN_CARRYCASCOUT}	ACIN input to CARRYCASCOUT output not using multiplier	1.61	1.85	2.21	2.84	ns
T _{DSPDO_PCIN_P}	PCIN input to P output	1.11	1.28	1.52	1.82	ns
T _{DSPDO_PCIN_CARRYCASCOUT}	PCIN input to CARRYCASCOUT output	1.36	1.56	1.85	2.21	ns
Clock to Outs from Output Register Clock to Output Pins						
T _{DSPCKO_P_PREG}	CLK PREG to P output	0.33	0.37	0.44	0.54	ns
T _{DSPCKO_CARRYCASCOUT_PREG}	CLK PREG to CARRYCASCOUT output	0.52	0.59	0.69	0.84	ns

Device Pin-to-Pin Output Parameter Guidelines

All devices are 100% functionally tested. Values are expressed in nanoseconds unless otherwise noted.

Table 36: Clock-Capable Clock Input to Output Delay Without MMCM/PLL (Near Clock Region)

Symbol	Description	Device	Speed Grade				Units
			1.0V			0.9V	
			-3	-2/-2L	-1	-2L	
SSTL15 Clock-Capable Clock Input to Output Delay using Output Flip-Flop, Fast Slew Rate, <i>without</i> MMCM/PLL.							
T _{ICKOF}	Clock-capable clock input and OUTFF <i>without</i> MMCM/PLL (near clock region)	XC7A100T	5.14	5.74	6.72	7.64	ns
		XC7A200T	5.47	6.11	7.16	8.10	ns

Notes:

1. Listed above are representative values where one global clock input drives one vertical clock line in each accessible column, and where all accessible IOB and CLB flip-flops are clocked by the global clock net.

Table 37: Clock-Capable Clock Input to Output Delay Without MMCM/PLL (Far Clock Region)

Symbol	Description	Device	Speed Grade				Units
			1.0V			0.9V	
			-3	-2/-2L	-1	-2L	
SSTL15 Clock-Capable Clock Input to Output Delay using Output Flip-Flop, Fast Slew Rate, <i>without</i> MMCM/PLL.							
T _{ICKOFFAR}	Clock-capable clock input and OUTFF <i>without</i> MMCM/PLL (far clock region)	XC7A100T	5.38	6.01	7.02	7.96	ns
		XC7A200T	6.17	6.89	8.05	9.05	ns

Notes:

1. Listed above are representative values where one global clock input drives one vertical clock line in each accessible column, and where all accessible IOB and CLB flip-flops are clocked by the global clock net.

Table 38: Clock-Capable Clock Input to Output Delay With MMCM

Symbol	Description	Device	Speed Grade				Units
			1.0V			0.9V	
			-3	-2/-2L	-1	-2L	
SSTL15 Clock-Capable Clock Input to Output Delay using Output Flip-Flop, Fast Slew Rate, <i>with</i> MMCM.							
T _{ICKOFMMCMCC}	Clock-capable clock input and OUTFF <i>with</i> MMCM	XC7A100T	0.89	0.94	0.96	1.81	ns
		XC7A200T	0.90	0.97	1.01	1.86	ns

Notes:

1. Listed above are representative values where one global clock input drives one vertical clock line in each accessible column, and where all accessible IOB and CLB flip-flops are clocked by the global clock net.
2. MMCM output jitter is already included in the timing calculation.

GTP Transceiver Specifications

GTP Transceiver DC Input and Output Levels

Table 47 summarizes the DC output specifications of the GTP transceivers in Artix-7 FPGAs. Consult [UG482: 7 Series FPGAs GTP Transceiver User Guide](#) for further details.

Table 47: GTP Transceiver DC Specifications

Symbol	DC Parameter	Conditions	Min	Typ	Max	Units
DV_{PPOUT}	Differential peak-to-peak output voltage ⁽¹⁾	Transmitter output swing is set to maximum setting	–	–	1000	mV
$V_{CMOUTDC}$	DC common mode output voltage	Equation based	$V_{MGTAVTT} - DV_{PPOUT}/4$			mV
R_{OUT}	Differential output resistance		–	100	–	Ω
$V_{CMOUTAC}$	Common mode output voltage: AC coupled		$1/2 V_{MGTAVTT}$			mV
T_{OSKEW}	Transmitter output pair (TXP and TXN) intra-pair skew (FFG, FBG, SBG packages)		–	–	10	ps
	Transmitter output pair (TXP and TXN) intra-pair skew (FGG, FTG, CSG packages)		–	–	12	ps
DV_{PPIN}	Differential peak-to-peak input voltage	External AC coupled	150	–	2000	mV
V_{IN}	Absolute input voltage	DC coupled $V_{MGTAVTT} = 1.2V$	–200	–	$V_{MGTAVTT}$	mV
V_{CMIN}	Common mode input voltage	DC coupled $V_{MGTAVTT} = 1.2V$	–	$2/3 V_{MGTAVTT}$	–	mV
R_{IN}	Differential input resistance		–	100	–	Ω
C_{EXT}	Recommended external AC coupling capacitor ⁽²⁾		–	100	–	nF

Notes:

- The output swing and preemphasis levels are programmable using the attributes discussed in [UG482: 7 Series FPGAs GTP Transceiver User Guide](#) and can result in values lower than reported in this table.
- Other values can be used as appropriate to conform to specific protocols and standards.

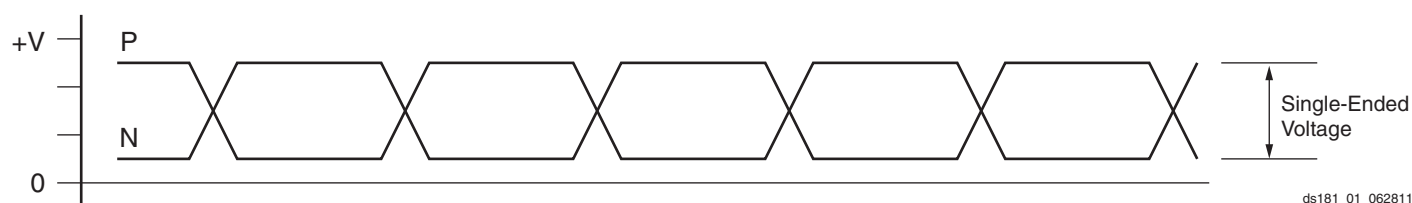


Figure 1: Single-Ended Peak-to-Peak Voltage

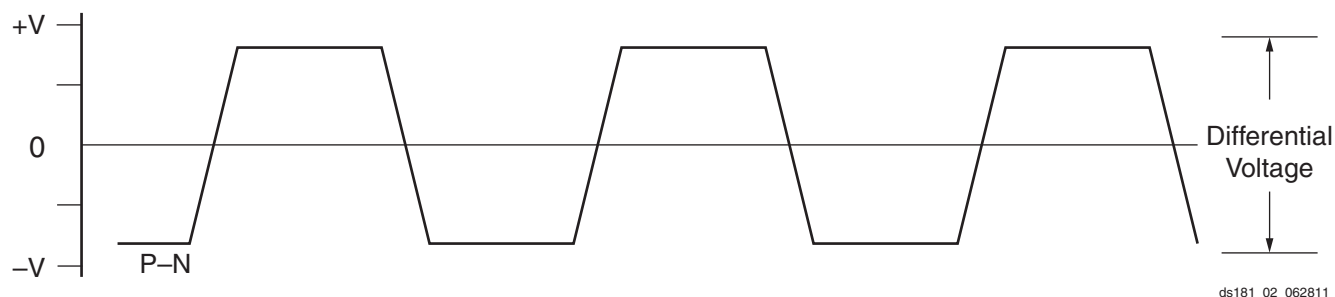


Figure 2: Differential Peak-to-Peak Voltage

Table 55: GTP Transceiver Receiver Switching Characteristics

Symbol	Description		Min	Typ	Max	Units
F _{GTPRX}	Serial data rate	RX oversampler not enabled	0.500	–	F _{GTPMAX}	Gb/s
T _{RXELECIDLE}	Time for RXELEC_IDLE to respond to loss or restoration of data		–	10	–	ns
RX _{OOBVDPP}	OOB detect threshold peak-to-peak		60	–	150	mV
RX _{SST}	Receiver spread-spectrum tracking ⁽¹⁾	Modulated @ 33 KHz	–5000	–	5000	ppm
RX _{RL}	Run length (CID)		–	–	512	UI
RX _{PPMTOL}	Data/REFCLK PPM offset tolerance		–1250	–	1250	ppm
SJ Jitter Tolerance ⁽²⁾						
JT_SJ _{6.6}	Sinusoidal Jitter ⁽³⁾	6.6 Gb/s	0.44	–	–	UI
JT_SJ _{5.0}	Sinusoidal Jitter ⁽³⁾	5.0 Gb/s	0.44	–	–	UI
JT_SJ _{4.25}	Sinusoidal Jitter ⁽³⁾	4.25 Gb/s	0.44	–	–	UI
JT_SJ _{3.75}	Sinusoidal Jitter ⁽³⁾	3.75 Gb/s	0.44	–	–	UI
JT_SJ _{3.2}	Sinusoidal Jitter ⁽³⁾	3.2 Gb/s ⁽⁴⁾	0.45	–	–	UI
JT_SJ _{3.2L}	Sinusoidal Jitter ⁽³⁾	3.2 Gb/s ⁽⁵⁾	0.45	–	–	UI
JT_SJ _{2.5}	Sinusoidal Jitter ⁽³⁾	2.5 Gb/s ⁽⁶⁾	0.5	–	–	UI
JT_SJ _{1.25}	Sinusoidal Jitter ⁽³⁾	1.25 Gb/s ⁽⁷⁾	0.5	–	–	UI
JT_SJ ₅₀₀	Sinusoidal Jitter ⁽³⁾	500 Mb/s	0.4	–	–	UI
SJ Jitter Tolerance with Stressed Eye ⁽²⁾						
JT_TJSE _{3.2}	Total Jitter with Stressed Eye ⁽⁸⁾	3.2 Gb/s	0.70	–	–	UI
JT_TJSE _{6.6}		6.6 Gb/s	0.70	–	–	UI
JT_SJSE _{3.2}	Sinusoidal Jitter with Stressed Eye ⁽⁸⁾	3.2 Gb/s	0.1	–	–	UI
JT_SJSE _{6.6}		6.6 Gb/s	0.1	–	–	UI

Notes:

- Using RXOUT_DIV = 1, 2, and 4.
- All jitter values are based on a bit error ratio of $1e^{-12}$.
- The frequency of the injected sinusoidal jitter is 10 MHz.
- PLL frequency at 3.2 GHz and RXOUT_DIV = 2.
- PLL frequency at 1.6 GHz and RXOUT_DIV = 1.
- PLL frequency at 2.5 GHz and RXOUT_DIV = 2.
- PLL frequency at 2.5 GHz and RXOUT_DIV = 4.
- Composite jitter.

Table 60: CPRI Protocol Characteristics

Description	Line Rate (Mb/s)	Min	Max	Units
CPRI Transmitter Jitter Generation				
Total transmitter jitter	614.4	–	0.35	UI
	1228.8	–	0.35	UI
	2457.6	–	0.35	UI
	3072.0	–	0.35	UI
	4915.2	–	0.3	UI
	6144.0	–	0.3	UI
CPRI Receiver Frequency Jitter Tolerance				
Total receiver jitter tolerance	614.4	0.65	–	UI
	1228.8	0.65	–	UI
	2457.6	0.65	–	UI
	3072.0	0.65	–	UI
	4915.2 ⁽¹⁾	0.60	–	UI
	6144.0 ⁽¹⁾	0.60	–	UI

Notes:

1. Tested to CEI-6G-SR.

Integrated Interface Block for PCI Express Designs Switching Characteristics

More information and documentation on solutions for PCI Express designs can be found at:

<http://www.xilinx.com/technology/protocols/pciexpress.htm>

Table 61: Maximum Performance for PCI Express Designs

Symbol	Description	Speed Grade				Units
		1.0V			0.9V	
		-3	-2/-2L	-1	-2L	
F _{PIPECLK}	Pipe clock maximum frequency	250.00	250.00	250.00	250.00	MHz
F _{USERCLK}	User clock maximum frequency	250.00	250.00	250.00	250.00	MHz
F _{USERCLK2}	User clock 2 maximum frequency	250.00	250.00	250.00	250.00	MHz
F _{DRPCLK}	DRP clock maximum frequency	250.00	250.00	250.00	250.00	MHz

Table 62: XADC Specifications (Cont'd)

Parameter	Symbol	Comments/Conditions	Min	Typ	Max	Units
DCLK Duty Cycle			40	–	60	%
XADC Reference⁽⁵⁾						
External Reference	V_{REFP}	Externally supplied reference voltage	1.20	1.25	1.30	V
On-Chip Reference		Ground V_{REFP} pin to AGND, $T_j = -40^{\circ}\text{C}$ to 100°C	1.2375	1.25	1.2625	V

Notes:

- Offset and gain errors are removed by enabling the XADC automatic gain calibration feature. The values are specified for when this feature is enabled.
- Only specified for BitGen option XADCEnhancedLinearity = ON.
- See the ADC chapter in [UG480: 7 Series FPGAs XADC User Guide](#) for a detailed description.
- See the Timing chapter in [UG480: 7 Series FPGAs XADC User Guide](#) for a detailed description.
- Any variation in the reference voltage from the nominal $V_{REFP} = 1.25\text{V}$ and $V_{REFN} = 0\text{V}$ will result in a deviation from the ideal transfer function. This also impacts the accuracy of the internal sensor measurements (i.e., temperature and power supply). However, for external ratiometric type applications allowing reference to vary by $\pm 4\%$ is permitted. On-chip reference variation is $\pm 1\%$.

Configuration Switching Characteristics

Table 63: Configuration Switching Characteristics

Symbol	Description	Speed Grade				Units
		1.0V			0.9V	
		-3	-2/-2L	-1	-2L	
Power-up Timing Characteristics						
T _{PL} ⁽¹⁾	Program latency	5.00	5.00	5.00	5.00	ms, Max
T _{POR} ⁽¹⁾	Power-on reset (50 ms ramp rate time)	10/50	10/50	10/50	10/50	ms, Min/Max
	Power-on reset (1 ms ramp rate time)	10/35	10/35	10/35	10/35	ms, Min/Max
T _{PROGRAM}	Program pulse width	250.00	250.00	250.00	250.00	ns, Min
CCLK Output (Master Mode)						
T _{ICCK}	Master CCLK output delay	150.00	150.00	150.00	150.00	ns, Min
T _{MCCKL}	Master CCLK clock Low time duty cycle	40/60	40/60	40/60	40/60	%, Min/Max
T _{MCCKH}	Master CCLK clock High time duty cycle	40/60	40/60	40/60	40/60	%, Min/Max
F _{MCCK}	Master CCLK frequency	100.00	100.00	100.00	70.00	MHz, Max
	Master CCLK frequency for AES encrypted x16	50.00	50.00	50.00	35.00	MHz, Max
F _{MCCK_START}	Master CCLK frequency at start of configuration	3.00	3.00	3.00	3.00	MHz, Typ
F _{MCCKTOL}	Frequency tolerance, master mode with respect to nominal CCLK	±50	±50	±50	±50	%, Max
CCLK Input (Slave Modes)						
T _{SCCKL}	Slave CCLK clock minimum Low time	2.50	2.50	2.50	2.50	ns, Min
T _{SCCKH}	Slave CCLK clock minimum High time	2.50	2.50	2.50	2.50	ns, Min
F _{SCCK}	Slave CCLK frequency	100.00	100.00	100.00	70.00	MHz, Max
EMCCLK Input (Master Mode)						
T _{EMCCKL}	External master CCLK Low time	2.50	2.50	2.50	2.50	ns, Min
T _{EMCCKH}	External master CCLK High time	2.50	2.50	2.50	2.50	ns, Min
F _{EMCCK}	External master CCLK frequency	100.00	100.00	100.00	70.00	MHz, Max

Table 63: Configuration Switching Characteristics (Cont'd)

Symbol	Description	Speed Grade				Units
		1.0V			0.9V	
		-3	-2/-2L	-1	-2L	
Internal Configuration Access Port						
F _{ICAPCK}	Internal configuration access port (ICAPE2) clock frequency	100.00	100.00	100.00	70.00	MHz, Max
Master/Slave Serial Mode Programming Switching						
T _{DCCK} /T _{CCKD}	DIN setup/hold	4.00/0.00	4.00/0.00	4.00/0.00	5.00/0.00	ns, Min
T _{CCO}	DOUT clock to out	8.00	8.00	8.00	9.00	ns, Max
SelectMAP Mode Programming Switching						
T _{SMDCCK} /T _{SMCCKD}	D[31:00] setup/hold	4.00/0.00	4.00/0.00	4.00/0.00	4.50/0.00	ns, Min
T _{SMCSCCK} /T _{SMCCCKS}	CSI_B setup/hold	4.00/0.00	4.00/0.00	4.00/0.00	5.00/0.00	ns, Min
T _{SMWCCK} /T _{SMCCKW}	RDWR_B setup/hold	10.00/0.00	10.00/0.00	10.00/0.00	12.00/0.00	ns, Min
T _{SMCKCSO}	CSO_B clock to out (330 Ω pull-up resistor required)	7.00	7.00	7.00	8.00	ns, Max
T _{SMCO}	D[31:00] clock to out in readback	8.00	8.00	8.00	10.00	ns, Max
F _{RBCK}	Readback frequency	100.00	100.00	100.00	70.00	MHz, Max
Boundary-Scan Port Timing Specifications						
T _{TAPTCK} /T _{TCKTAP}	TMS and TDI setup/hold	3.00/2.00	3.00/2.00	3.00/2.00	3.00/2.00	ns, Min
T _{TCKTDO}	TCK falling edge to TDO output	7.00	7.00	7.00	8.50	ns, Max
F _{TCK}	TCK frequency	66.00	66.00	66.00	50.00	MHz, Max
BPI Flash Master Mode Programming Switching						
T _{BPICCO} ⁽²⁾	A[28:00], RS[1:0], FCS_B, FOE_B, FWE_B, ADV_B clock to out	8.50	8.50	8.50	10.00	ns, Max
T _{BPIDCC} /T _{BPICCD}	D[15:00] setup/hold	4.00/0.00	4.00/0.00	4.00/0.00	4.50/0.00	ns, Min
SPI Flash Master Mode Programming Switching						
T _{SPIDCC} /T _{SPICCD}	D[03:00] setup/hold	3.00/0.00	3.00/0.00	3.00/0.00	3.00/0.00	ns, Min
T _{SPICCM}	MOSI clock to out	8.00	8.00	8.00	9.00	ns, Max
T _{SPICCF}	FCS_B clock to out	8.00	8.00	8.00	9.00	ns, Max

Notes:

1. To support longer delays in configuration, use the design solutions described in [UG470: 7 Series FPGA Configuration User Guide](#).
2. Only during configuration, the last edge is determined by a weak pull-up/pull-down resistor in the I/O.

eFUSE Programming Conditions

Table 64 lists the programming conditions specifically for eFUSE. For more information, see [UG470: 7 Series FPGA Configuration User Guide](#).

Table 64: eFUSE Programming Conditions⁽¹⁾

Symbol	Description	Min	Typ	Max	Units
I _{FS}	V _{CCAUX} supply current	—	—	115	mA
t _j	Temperature range	15	—	125	°C

Notes:

1. The FPGA must not be configured during eFUSE programming.

Date	Version	Description
09/20/12	1.4	In Table 1, updated the descriptions, changed V_{IN} and Note 2, and added Note 4. In Table 2, changed descriptions and notes. Updated parameters in Table 3. Added Table 4. Revised the Power-On/Off Power Supply Sequencing section. Updated standards and specifications in Table 8, Table 9, and Table 10. Removed the XC7A350T device from data sheet. Updated the AC Switching Characteristics section to the ISE 14.2 speed specifications throughout the document. Updated the IOB Pad Input/Output/3-State discussion and changed Table 17 by adding $T_{IOIBUFDISABLE}$. Removed many of the combinatorial delay specifications and T_{CINCK}/T_{CKCIN} from Table 24. Changed F_{PFDMAX} conditions in Table 34 and Table 35. Updated the GTP Transceiver Specifications section, moved the GTP Transceiver DC characteristics section to the overall DC Characteristics section, and added the GTP Transceiver Protocol Jitter Characteristics section. In Table 62, updated Note 1. In Table 63, updated T_{POR}.
02/01/13	1.5	Updated the AC Switching Characteristics based upon the 14.4/2012.4 device pack for ISE 14.4 and Vivado 2012.4, both at v1.07 for the -3, -2, -2L (1.0V), -1 speed specifications, and v1.05 for the -2L (0.9V) speed specifications throughout the document. Production changes to Table 12 and Table 13 for -3, -2, -2L (1.0V), -1 speed specifications. Revised I_{DCIN} and I_{DCOUT} and added Note 5 in Table 1. Added Note 2 to Table 2. Updated Table 5. Added minimum current specifications to Table 6. Removed SSTL12 and HSTL_I_12 from Table 8. Removed DIFF_SSTL12 from Table 10. Updated Table 12. Added a 2:1 memory controller section to Table 15. Updated Note 1 in Table 31. Revised Table 33. Updated Note 1 and Note 2 in Table 46. Updated D_{VPPIN} in Table 47. Updated V_{IDIFF} in Table 48. Removed T_{LOCK} and T_{PHASE} and revised F_{GCLK} in Table 51. Updated T_{DLOCK} in Table 52. Updated Table 53. In Table 54, updated T_{RTX}, T_{FTX}, $V_{TXOVBVDDP}$, and revised Note 1 through Note 7. In Table 55, updated RX_{SST} and RX_{PPMTOL} and revised Note 4 through Note 7. In Table 60, revised and added Note 1. Revised the maximum external channel input ranges in Table 62. In Table 63, revised F_{MCCK} and added the Internal Configuration Access Port section.